

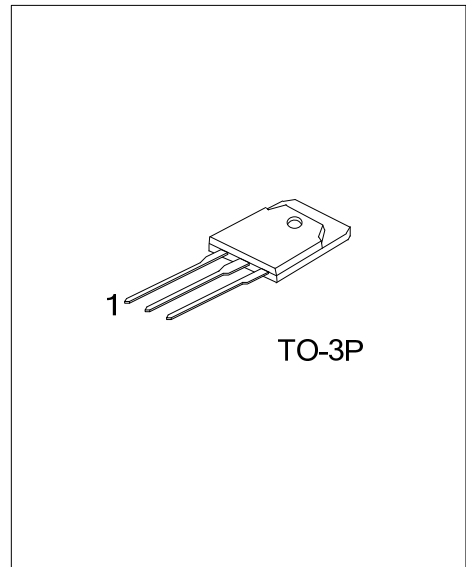


2SC4466

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

SILICON NPN TRIPLE DIFFUSED PLANAR TRANSISTOR



DESCRIPTION

The UTC **2SC4466** is a silicon NPN triple diffused planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-base breakdown voltage, etc.

The UTC **2SC4466** is suitable for audio and general purpose, etc.

FEATURES

- * High DC current gain
- * High collector-base breakdown voltage

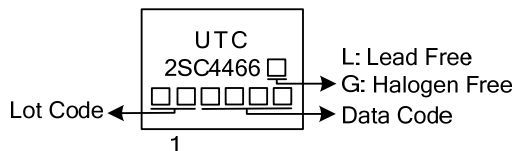
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC4466L-x-T3P-T	2SC4466G-x-T3P-T	TO-3P	B	C	E	Tube

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SC4466L-x-T3P-T</p>	<p>(1) T: Tube (2) T3P: TO-3P (3) x: reference to Classification of h_{FE} (4) L: Lead Free, G: Halogen Free and Lead Free</p>
-------------------------	---

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	6	A
Base Current	I_B	3	A
Collector Power Dissipation ($T_C=25^\circ\text{C}$)	P_C	60	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

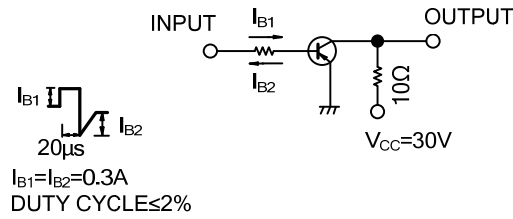
■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I_{CBO}	$V_{CB}=120\text{V}$			10	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=6\text{V}$			10	μA
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=50\text{mA}$	80			V
DC Current Gain	h_{FE}	$V_{CE}=4\text{V}, I_C=2\text{A}$	50		180	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=2\text{A}, I_B=0.2\text{A}$			1.5	V
Current Gain Bandwidth Product	f_T	$V_{CE}=12\text{V}, I_E=-0.5\text{A}$		20		MHz
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$		110		pF
Switching time	Turn-on time	$V_{CC}=30\text{V}, R_L=10\Omega, I_C=3\text{A},$ $I_{B1}=0.3\text{A}, I_{B2}=0.3\text{A}$		0.16		μS
	Storage time			2.60		μS
	Fall time			0.34		μS

■ CLASSIFICATION OF h_{FE}

RANK	O	P	Y
RANGE	50~100	70~140	90~180

■ TEST CIRCUIT



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.